

## **General Description**

The DMG6968UTS-13 is the highest performance trench

N-ch MOSFETs with extreme high cell density, which

provide excellent RDSON and gate charge for most

of the small power switching and load switch applications.

The meet the RoHS and Product requirement with full function reliability approved.

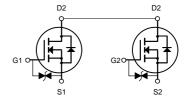


 $V_{DS} = 20V I_{D} = 7A$ 

 $R_{DS(ON)}$  < 14m $\Omega$  @  $V_{GS}$ =4. 5V

 $R_{DS(ON)}$  < 17m $\Omega$  @ V<sub>GS</sub>=2. 5V

#### S2 D2 S2 D2 S2 D2 S1 Pin 1 TSSOP-8



#### **Dual N-Channel MOSFET**

## **Application**

Battery protection

Load switch

Uninterruptible power supply

## **Package Marking and Ordering Information**

Product ID	Pack	Brand	Qty(PCS)
DMG6968UTS-13	TSSOP-8	HXY MOSFET	5000

## Absolute Maximum Ratings (TA=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit	
V <sub>DS</sub>	Drain-Source Voltage	20	V	
V <sub>G</sub> s	Gate-Source Voltage	±10	V	
I <sub>D</sub>	Drain Current-Continuous	7	Α	
Ірм	Drain Current-Pulsed (Note 1)	23	Α	
P <sub>D</sub>	Maximum Power Dissipation	1.25	W	
TJ,Tstg	Operating Junction and Storage Temperature Range	-55 To 150	°C	
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	111	°C/W	

## Dual N-Channel Enhancement Mode MOSFET

# Electrical Characteristics (T<sub>A</sub>=25 ℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	20	-	-	V
Zero Gate Voltage Drain Current	Ipss	V <sub>DS</sub> =16V,V <sub>GS</sub> =0V	-	-	1	μΑ
Gate-Body Leakage Current	Igss	V <sub>GS</sub> =±8V,V <sub>DS</sub> =0V	-	-	±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250μA	0.5	0.7	1.2	V
	Rds(on)	V <sub>GS</sub> =4.5V, I <sub>D</sub> =4.5A	-	12	14	mΩ
Drain-Source On-State Resistance		V <sub>GS</sub> =2.5V, I <sub>D</sub> =3.5A	-	15	17	mΩ
Forward Transconductance	grs	V <sub>DS</sub> =5V,I <sub>D</sub> =3.5A	-	20	-	S
Input Capacitance	C <sub>lss</sub>		-	955	-	PF
Output Capacitance	Coss	V <sub>DS</sub> =8V,V <sub>GS</sub> =0V,	-	200	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	150	-	PF
Turn-on Delay Time	td(on)		-	8		nS
Turn-on Rise Time	tr	V <sub>DD</sub> =10V,I <sub>D</sub> =3.5A	-	17	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}=10V, I_{D}=3.5A$ $V_{GS}=4.5V, R_{GEN}=6\Omega$	-	27	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	8.8	-	nS
Total Gate Charge	Qg		-	11.3	-	nC
Gate-Source Charge	Qgs	V <sub>DS</sub> =10V,I <sub>D</sub> =7A,	-	1.89	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =4.5V	-	3.56	-	nC
Diode Forward Voltage (Note 3)	VsD	V <sub>GS</sub> =0V,I <sub>S</sub> =1.7A	-	0.75	1.2	V
Diode Forward Current (Note 2)	Is		-	-	7	Α

#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤  $300\mu$ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



# **Typical Characteristics**

Figure1: Output Characteristics

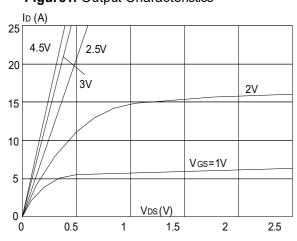


Figure 2: Typical Transfer Characteristics

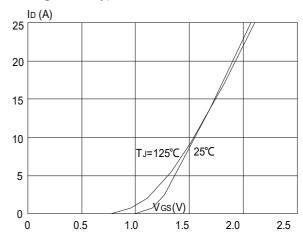


Figure 3:On-resistance vs. Drain Current

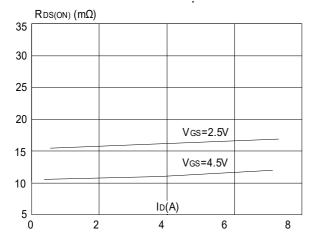


Figure 4: Body Diode Characteristics

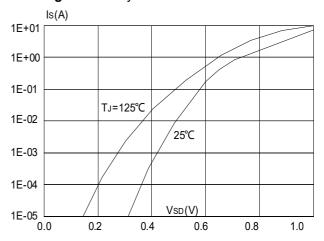


Figure 5: Gate Charge Characteristics

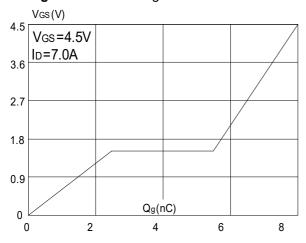
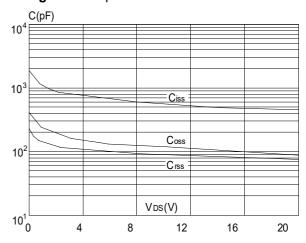
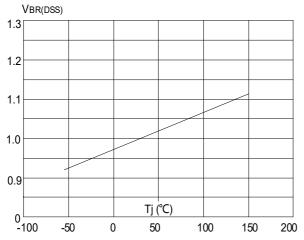


Figure 6: Capacitance Characteristics





**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



**Figure 8:** Normalized on Resistance vs. Junction Temperature

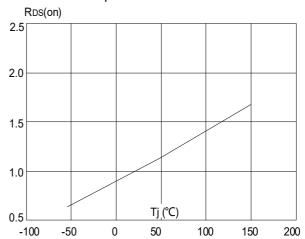
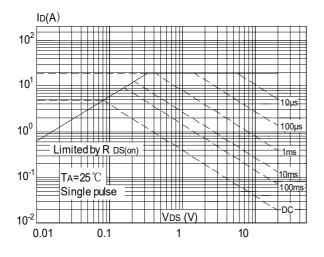
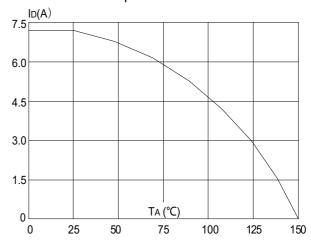


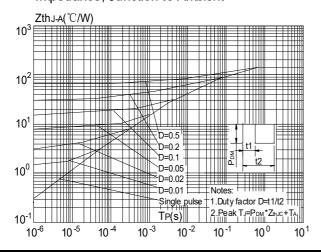
Figure 9: Maximum Safe Operating Area



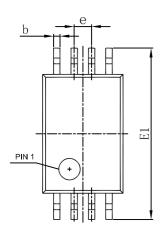
**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature

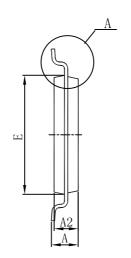


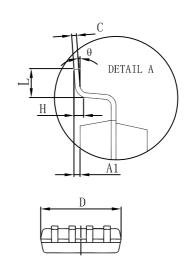
**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



# **TSSOP-8 Package Outline Dimensions**







Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
D	2.900	3. 100	0. 114	0.122	
Е	4.300	4. 500	0. 169	0.177	
b	0.190	0.300	0.007	0.012	
С	0.090	0. 200	0.004	0.008	
E1	6.250	6. 550	0. 246	0.258	
A		1. 200		0.047	
A2	0.800	1.000	0.031	0.039	
A1	0.050	0. 150	0.002	0.006	
e	0.65 (BSC)		0. 026 (BSC)		
L	0.500	0.700	0. 020	0.028	
Н	0.25(TYP)		0.01(TYP)		
θ	1°	7°	1 °	7°	

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